

N-Channel Enhancement Mode MOSFET

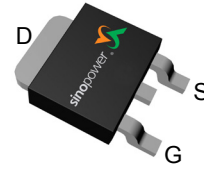
Features

- 100V/30A
 $R_{DS(ON)}=26.4m\Omega(max.)@V_{GS}=10V$
 $R_{DS(ON)}=34.5m\Omega(max.)@V_{GS}=4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

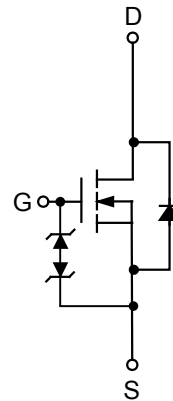
Applications

- For telecom PSE solution.

Pin Description

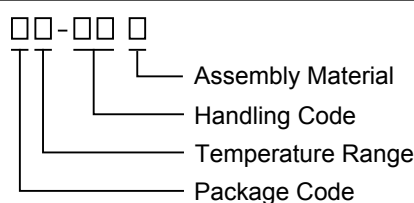



TO-252-2



N-Channel MOSFET

Ordering and Marking Information

<p>SM1A68NH □□-□□ □</p>  <p>Assembly Material Handling Code Temperature Range Package Code</p>	<p>Package Code U : TO-252-2 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device</p>
<p>SM1A68NH U :</p>	 <p>XXXXX - Lot Code</p>

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the leadfree requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
Common Ratings			
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 15	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 30	A
		$T_C=100^\circ\text{C}$ 18.5	
I_{DM}^a	Pulsed Drain Current	$T_C=25^\circ\text{C}$ 120	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 52	W
		$T_C=100^\circ\text{C}$ 20	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.4	$^\circ\text{C}/\text{W}$
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$ 6.5	A
		$T_A=70^\circ\text{C}$ 5.2	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 2.5	W
		$T_A=70^\circ\text{C}$ 1.6	
$R_{\theta JA}^c$	Thermal Resistance-Junction to Ambient	50	$^\circ\text{C}/\text{W}$
I_{AS}^b	Avalanche Current, Single pulse	$L=0.5\text{mH}$ 12	A
E_{AS}^b	Avalanche Energy, Single pulse	$L=0.5\text{mH}$ 36	mJ

Note a : Pulse width limited by maximum junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

Note c : Surface Mounted on 1in^2 pad area.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

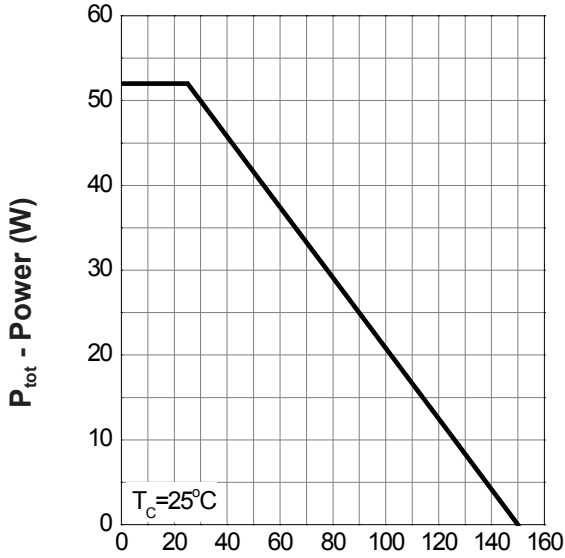
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=80V, V_{GS}=0V$	-	-	1	μA
		$T_J=85^\circ C$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1	2	3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 10	μA
$R_{DS(ON)}^d$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=15A$	-	22	26.4	$m\Omega$
		$V_{GS}=4.5V, I_{DS}=10A$	-	26.5	34.5	$m\Omega$
Diode Characteristics						
V_{SD}^d	Diode Forward Voltage	$I_{SD}=7A, V_{GS}=0V$	-	0.8	1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD}=15A, dI_{SD}/dt=100A/\mu s$	-	50	-	ns
Q_{rr}	Reverse Recovery Charge		-	50	-	nC
Dynamic Characteristics^e						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	1.5	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz	-	800	1040	pF
C_{oss}	Output Capacitance		-	195	-	
C_{rss}	Reverse Transfer Capacitance		-	15	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=30V, R_L=30\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=6\Omega$	-	12	22	ns
t_r	Turn-on Rise Time		-	6	11	
$t_{d(OFF)}$	Turn-off Delay Time		-	24	44	
t_f	Turn-off Fall Time		-	21	38	
Gate Charge Characteristics^e						
Q_g	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V,$ $I_{DS}=15A$	-	15.5	21.7	nC
Q_g	Total Gate Charge	$V_{DS}=50V, V_{GS}=4.5V,$ $I_{DS}=15A$	-	7.5	-	
Q_{gs}	Gate-Source Charge		-	3.0	-	
Q_{gd}	Gate-Drain Charge		-	3.2	-	

Note d : Pulse test ; pulse width \leq 300ms, duty cycle \leq 2%.

Note e : Guaranteed by design, not subject to production testing.

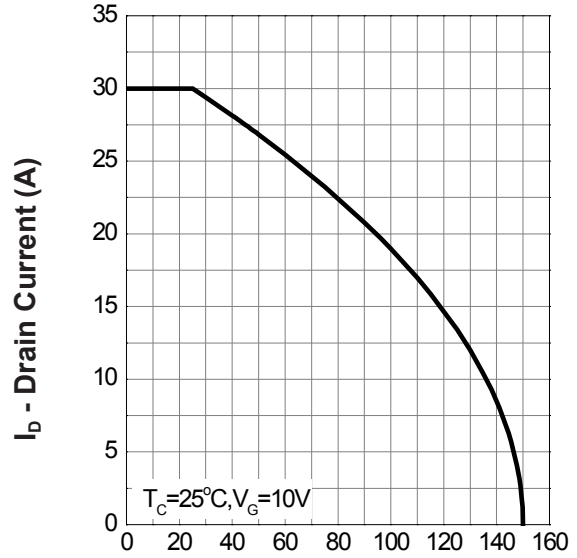
Typical Operating Characteristics

Power Dissipation



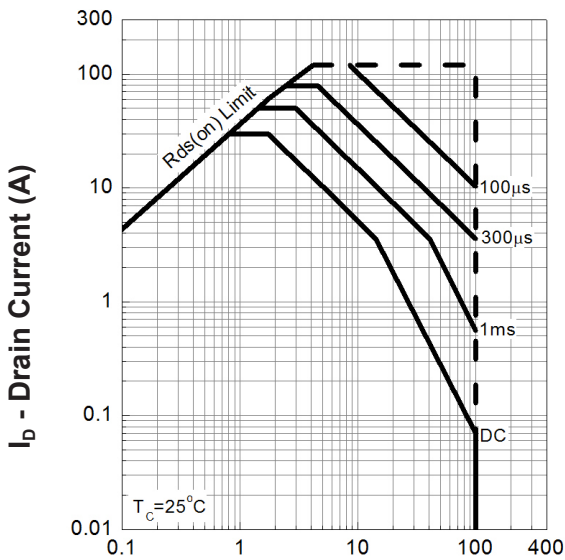
T_j - Junction Temperature (°C)

Drain Current



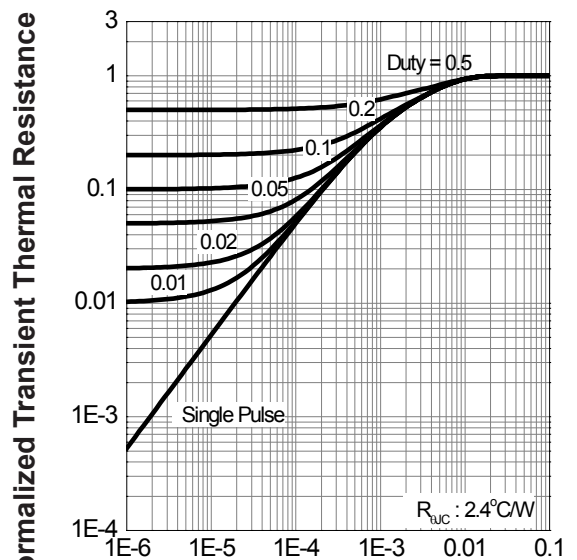
T_j - Junction Temperature (°C)

Safe Operation Area



V_{DS} - Drain - Source Voltage (V)

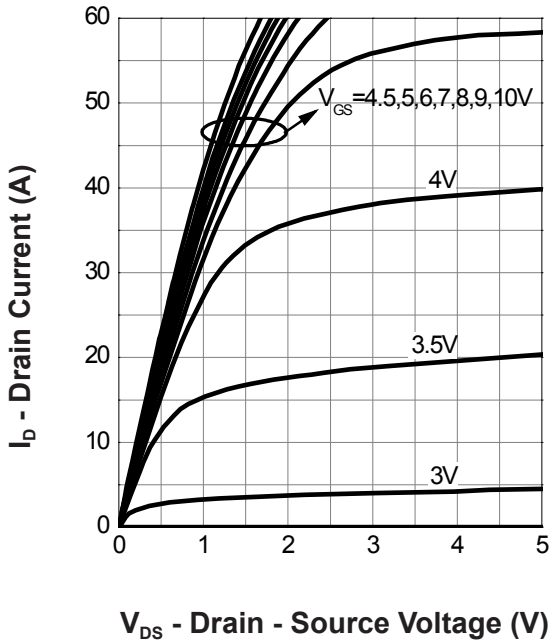
Thermal Transient Impedance



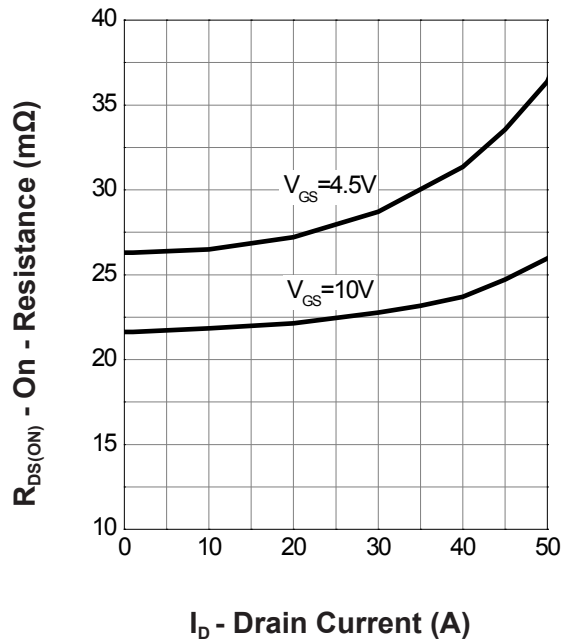
Square Wave Pulse Duration (sec)

Typical Operating Characteristics(Cont.)

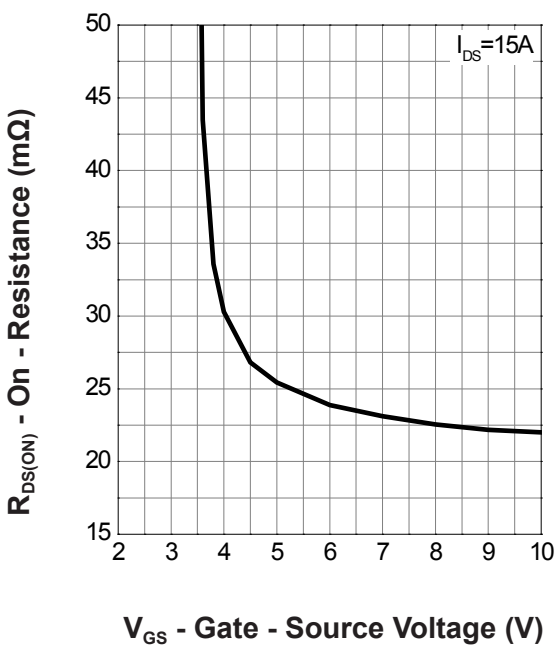
Output Characteristics



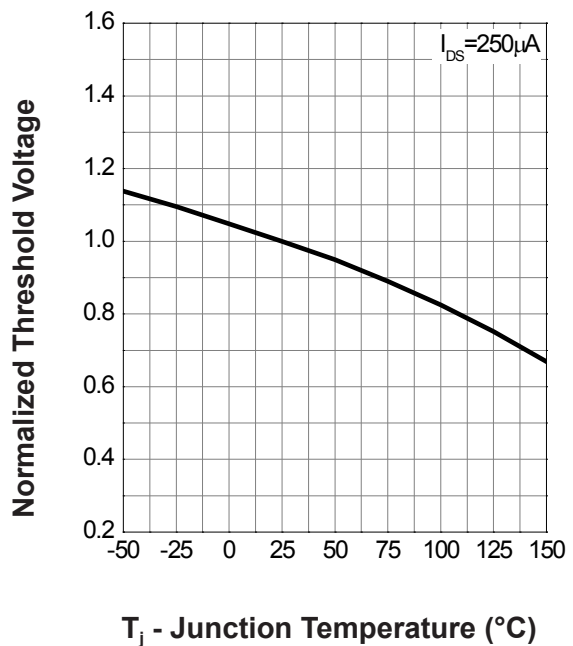
Drain-Source On Resistance



Gate-Source On Resistance

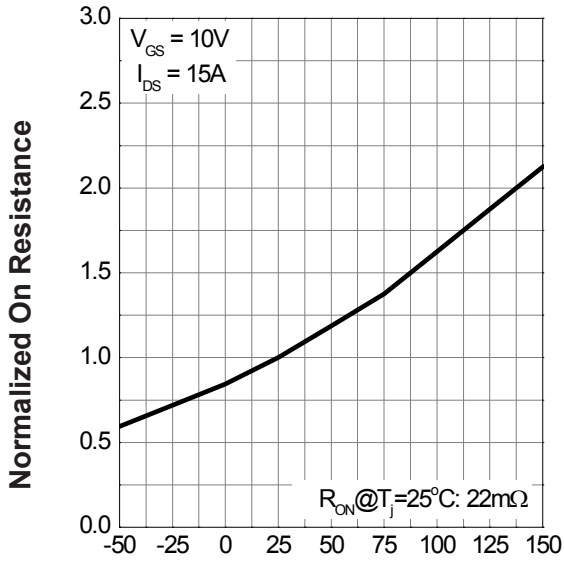


Gate Threshold Voltage



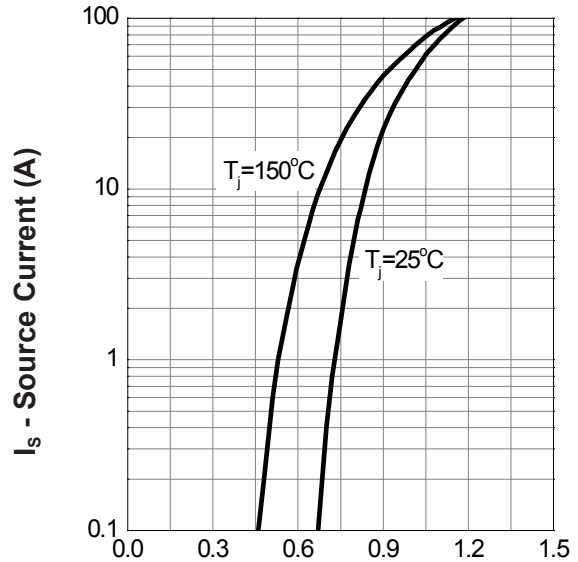
Typical Operating Characteristics(Cont.)

Drain-Source On Resistance



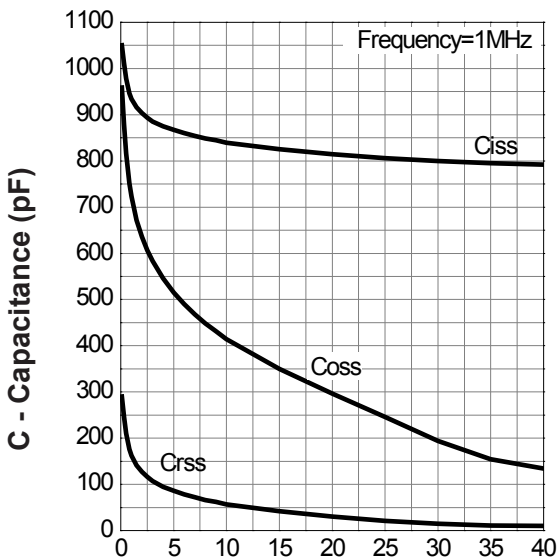
T_j - Junction Temperature (°C)

Source-Drain Diode Forward



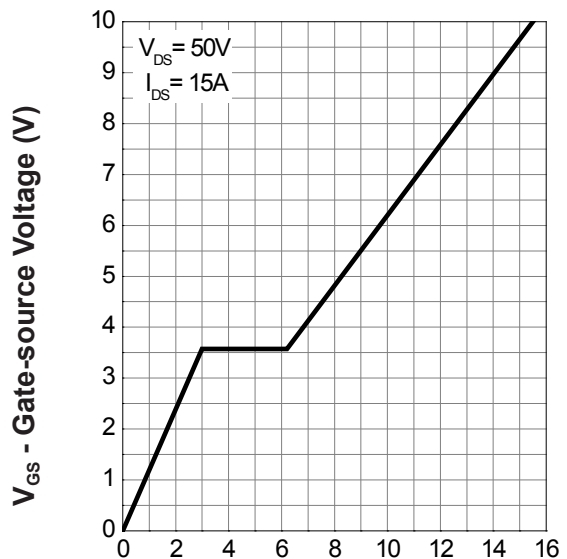
V_{SD} - Source - Drain Voltage (V)

Capacitance



V_{DS} - Drain-Source Voltage (V)

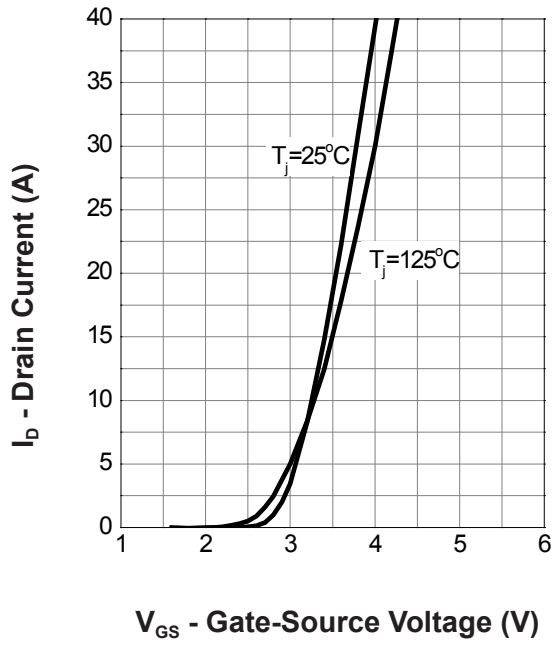
Gate Charge



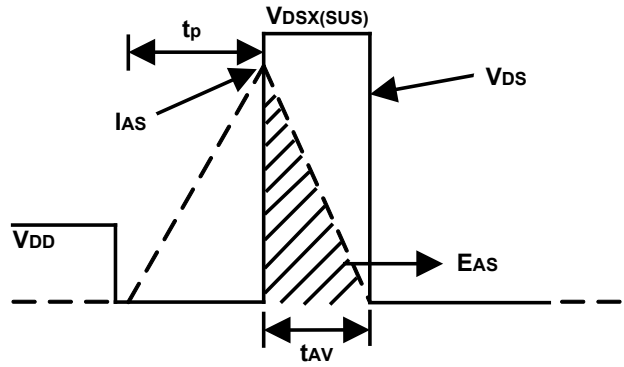
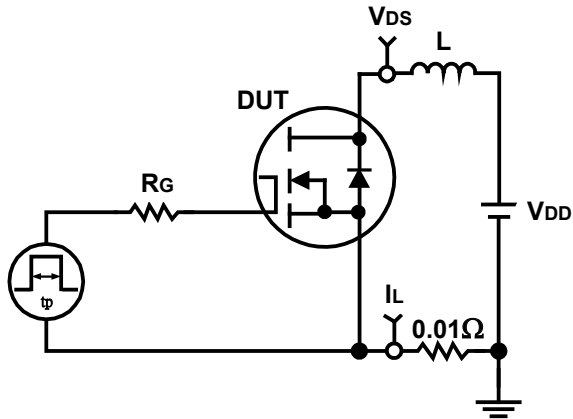
Q_G - Gate Charge (nC)

Typical Operating Characteristics(Cont.)

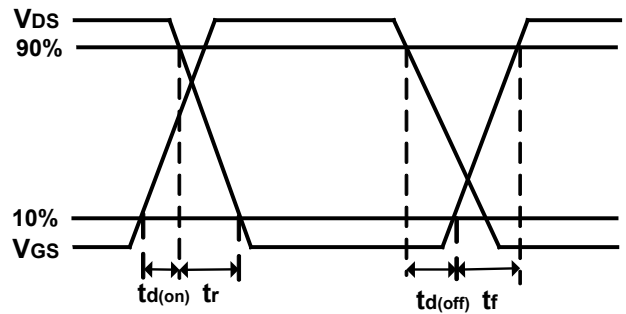
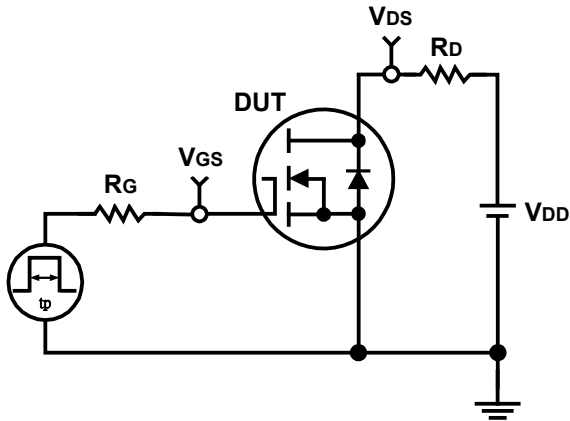
Transfer Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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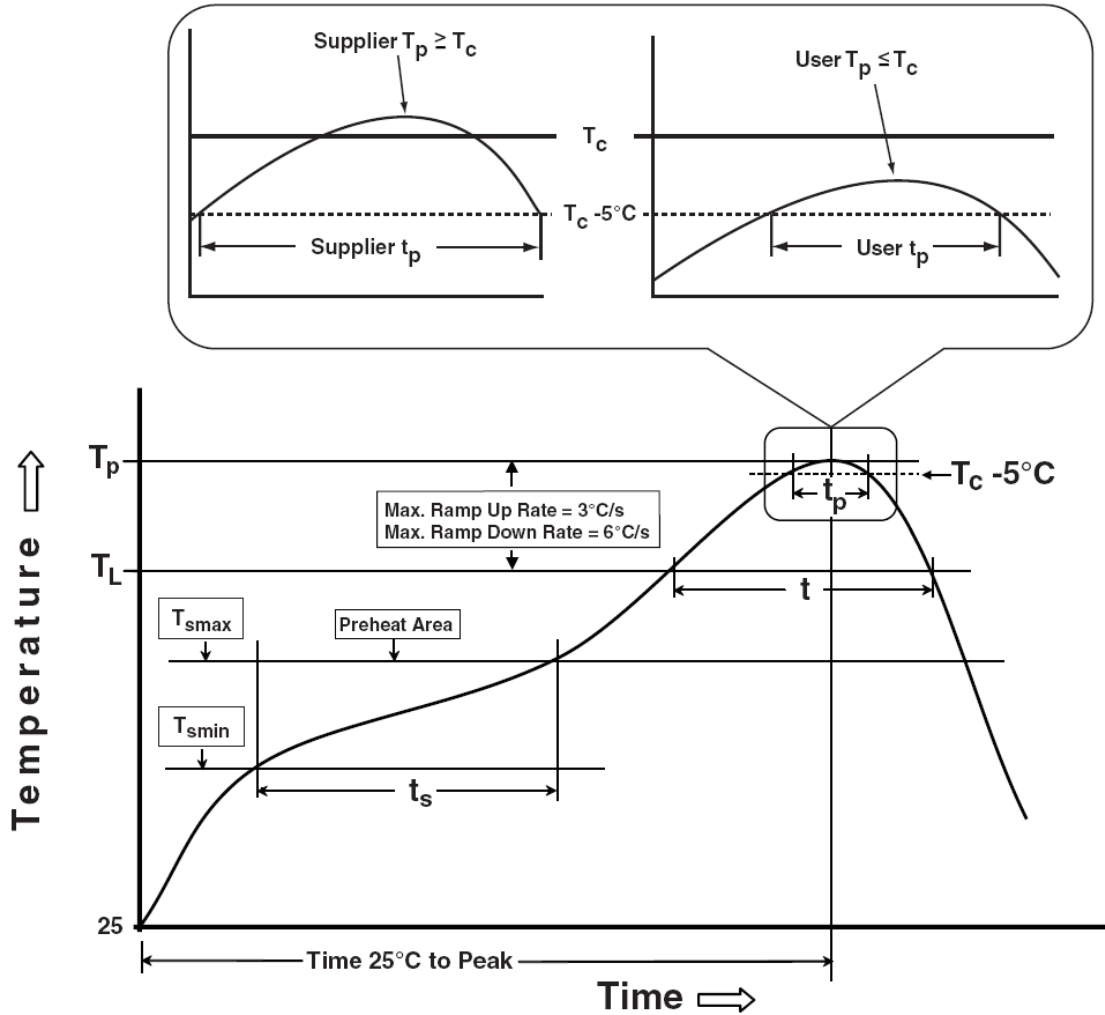
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

Sinopower Semiconductor, Inc.

5F, No. 6, Dusing 1St Rd., Hsinchu Science Park,
Hsinchu, 30078, Taiwan
TEL: 886-3-5635818 Fax: 886-3-5635080